wherein an amount of sodium contained within the wiring is equal to or less than 0.3

ppm.

2. (Amended) A device according to claim 1, wherein a thickness of the tungsten nitride film is 10 to 50 nm and a thickness of the tungsten film is 200 to 400 nm.

3. (Twice Amended) A device according to claim 1, wherein electrical resistivity of the wiring is equal to or less than 40 $\mu\Omega$ cm.

4. (Twice Amended) A semiconductor device comprising:

a wiring formed over a substrate, the wirings comprising a metal film and a nitride film of the metal film, the metal film located on the nitride film,

wherein the wiring includes at least one inert element and 90% or more of the inert element is argon, and

wherein an amount of sodium contained within the wiring is equal to or less than 0.3 ppm.

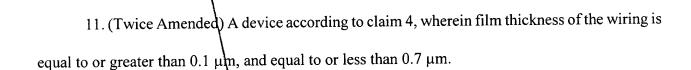
- 5. (Twice Amended) A device according to claim 4, further comprising a semiconductor film adjacent to the wiring with an insulating film interposed therebetween.
- 6. (Twice Amended) A device according to claim 4, wherein the inert element except for argon is contained within the wiring at an amount equal to or less than 1 atom%.

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7. (Twice Amended) A device according to claim 4, wherein the inert element except for argon is contained within the wiring at an amount equal to or less than 0.1 atom%.

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- 9. (Twice Amended) A device according to claim 4, wherein internal stress of the wiring is from -1 x 10^{10} dyn/cm² to +1 x 10^{10} dyn/cm².
- 10. (Twice Amended) A device according to claim 4, wherein line width of the wiring is equal to or less than 5 μ m.



- 12. (Twice Amended) A device according to claim 4, wherein the wiring is used as a gate electrode of a TFT.
- 13. (Twice Amended) A device according to claim 4, wherein resistance value per 1 square μm of surface area of a connection between the wiring and an aluminum wiring is equal to or less than 40 Ω .

16. (Twice Amended) A semiconductor device comprising:

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a wiring formed over a substrate, the wiring comprising a tungsten nitride film and a tungsten film formed thereon; and

an insulating film formed over the wiring, said insulating film comprising SiOxNy,

wherein the wiring includes at least one inert element and 90% or more of the inert

Cub dlement is argon, and

ppm.

wherein an amount of sodium contained within the wiring is equal to or less than 0.3

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- 17. (Twice Amended) A device according to claim 16, further comprising a semiconductor film adjacent to the wiring with an insulating film interposed therebetween.
- 18. (Twice Amended) A device according to claim 16, wherein the inert element except for argon is contained within the wiring at an amount equal to or less than 1 atom%.
- 19. (Twice Amended) A device according to claim 16, wherein the inert element except for argon is contained within the wiring at an amount equal to or less than 0.1 atom%.
- 21. (Twice Amended) A device according to claim 16, wherein internal stress of the tungsten film or of the wiring is from -1 x 10^{10} dyn/cm² to +1 x 10^{10} dyn/cm².



- 22. (Twice Amended) A device according to claim 16, wherein line width of the wiring is equal to or less than 5 μ m.
- 23. (Twice Amended) A device according to claim , wherein film thickness of the wiring is equal to or greater than 0.1 μ m, and equal to or less than 0.7 μ m.

24. (Twice Amended) A device according to claim 16, wherein the wiring is used as a gate electrode of a TFT.

25. (Twice Amended) A device according to claim 16, wherein resistance value per 1 square μm of surface area of a connection between the wiring and an aluminum wiring is equal to or less than 40 Ω .

28. (Twice Amended) A semiconductor device comprising:

a wiring formed over a substrate having a lamination structure comprising a phosphorus doped silicon, a nitride film of tungsten, and a film comprising tungsten,

wherein the film comprising tungsten includes at least one inert element, and 90% or more of the inert element is argon, and

wherein an amount of sodium contained within the wiring is equal to or less than 0.3 ppm.

36. (Amended) A device according to claim 28, wherein the wiring is used as a gate electrode of a TFT.

40. (Twice Amended) A semiconductor device comprising:

a wiring formed over a substrate, the wiring having a lamination structure containing a tungsten nitride film and a film comprising tungsten formed thereon,

wherein the film comprising tungsten includes at least one inert element, and 90% or more of the inert element is argon,